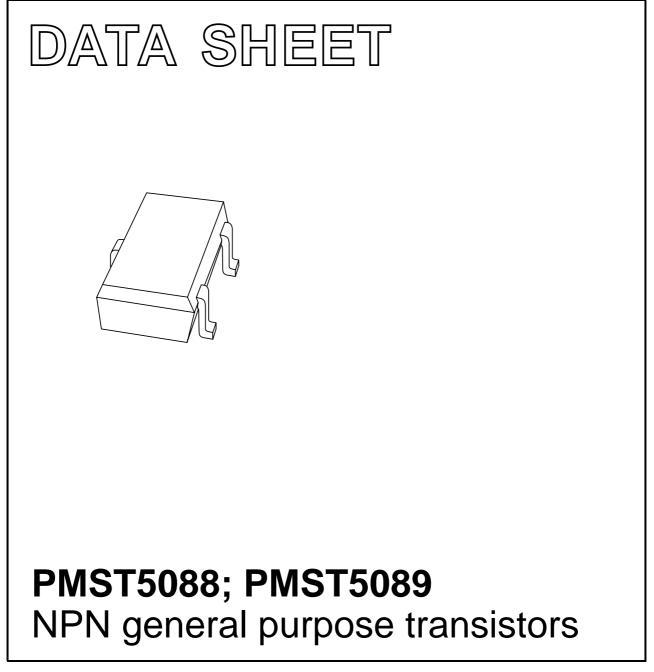
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 May 22 1999 Apr 22



NPN general purpose transistors

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 30 V).

APPLICATIONS

• Low-noise input stages in audio equipment.

DESCRIPTION

NPN transistor in a SC-70; SOT323 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST5088	*1Q
PMST5089	*1R

Note

- 1. * = : Made in Hong Kong.
 - * = t : Made in Malaysia.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	PMST5088		_	35	V
	PMST5089		-	30	V
V _{CEO}	collector-emitter voltage	open base			
	PMST5088		-	30	V
	PMST5089		_	25	V
V _{EBO}	emitter-base voltage	open collector	-	4.5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

Top view

MAM062

Fig.1 Simplified outline (SC-70; SOT323) and symbol.

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	

PMST5088; PMST5089

NPN general purpose transistors

PMST5088; PMST5089

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

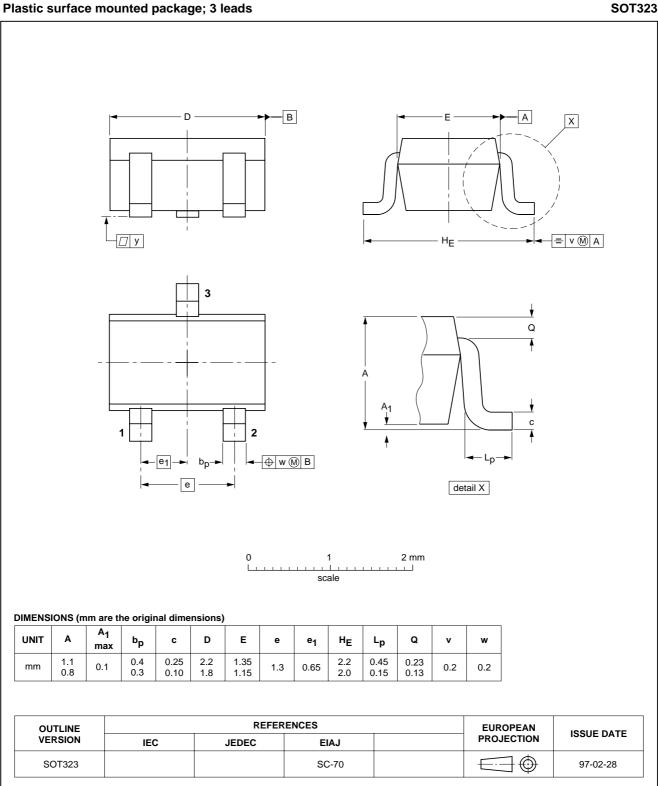
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	-	50	nA
		I _E = 0; V _{CB} = 20 V; T _j = 150 °C	-	10	μA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 3 V	-	50	nA
		I _C = 0; V _{EB} = 4.5 V	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V			
	PMST5088	$I_{\rm C} = 0.1 {\rm mA}$	300	900	
		$I_{C} = 1 \text{ mA}$	350	_	
		I _C = 10 mA	300	_	
	DC current gain	$V_{CE} = 5 V$			
	PMST5089	I _C = 0.1 mA	400	1200	
		$I_{\rm C} = 1 \rm{mA}$	450	-	
		I _C = 10 mA	400	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	-	500	mV
V _{BE}	base-emitter voltage	I _C = 10 mA; V _{CE} = 5 V	-	800	mV
Cc	collector capacitance	$I_E = i_e = 0; V_{CB} = 5 V; f = 1 MHz$	-	4	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$	-	12	pF
f _T	transition frequency	$I_{C} = 10 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ f} = 100 \text{ MHz}$	100	-	MHz
F	noise figure	I_C = 100 μ A; V_{CE} = 5 V; R_S = 1 k Ω			
	PMST5088	f = 10 Hz to 15.7 kHz	-	3	dB
	PMST5089		_	2	dB

PMST5088; PMST5089

NPN general purpose transistors

PACKAGE OUTLINE



SOT323

NPN general purpose transistors

PMST5088; PMST5089

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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Printed in The Netherlands

115002/00/03/pp6

Date of release: 1999 Apr 22

Document order number: 9397 750 05709

